

# **Supply-Variation-Tolerant Transimpedance Amplifier Using Non-Inverting Amplifier in 180-nm CMOS**



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- Background
- Comparing the reference TIA and the proposed TIA
- Design of the proposed TIA
- Measurement result
- Conclusion

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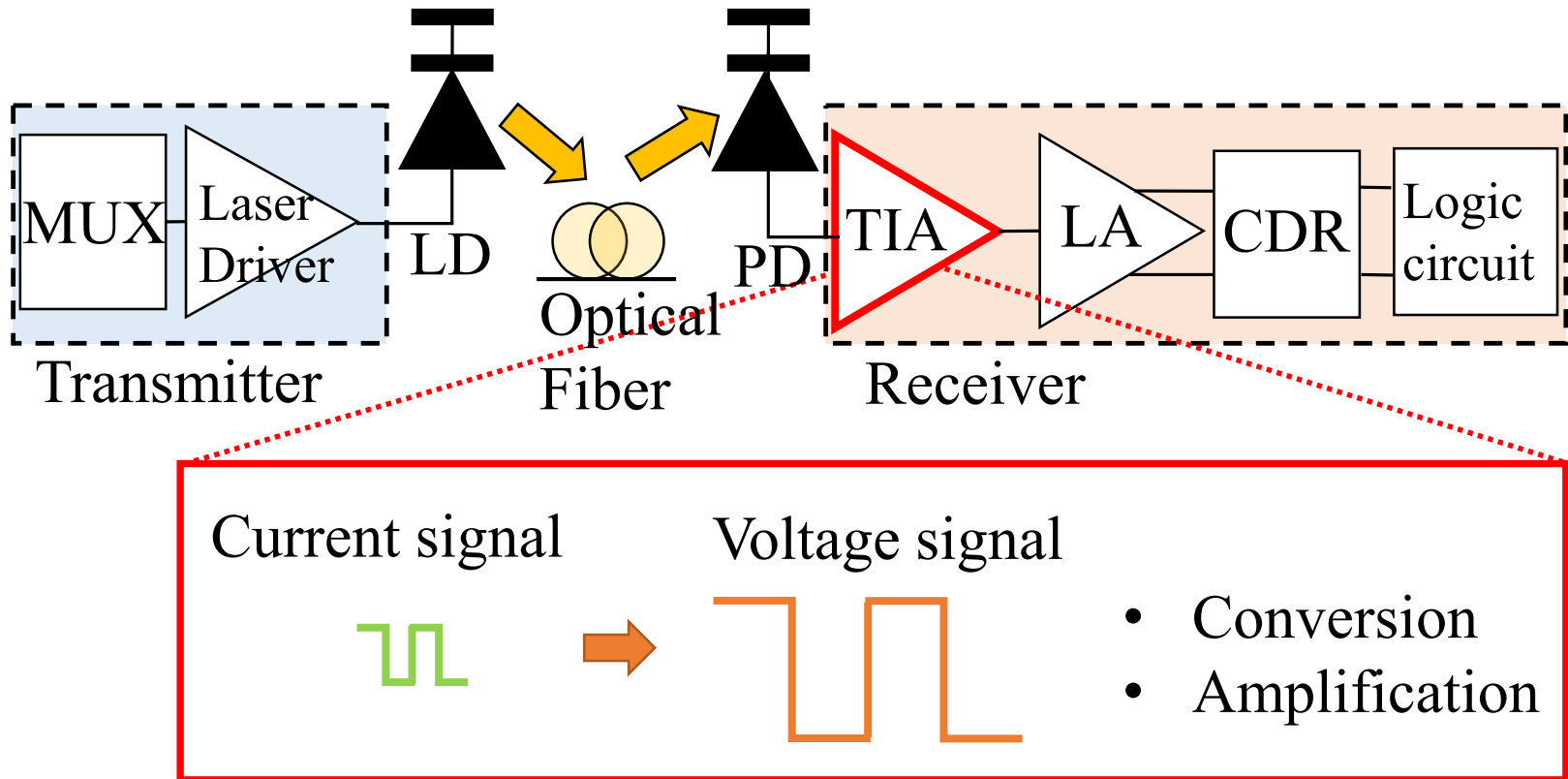
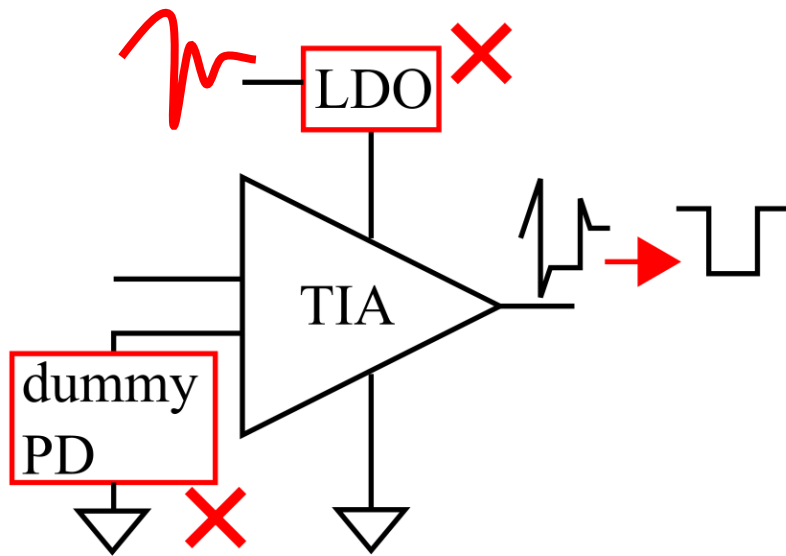


Fig. Overview of Optical Communication Systems.

Power Supply Noise Affects TIA Output.

➔ The bit error rate increases.

Commonly, power supply noise reduction uses extra circuits.



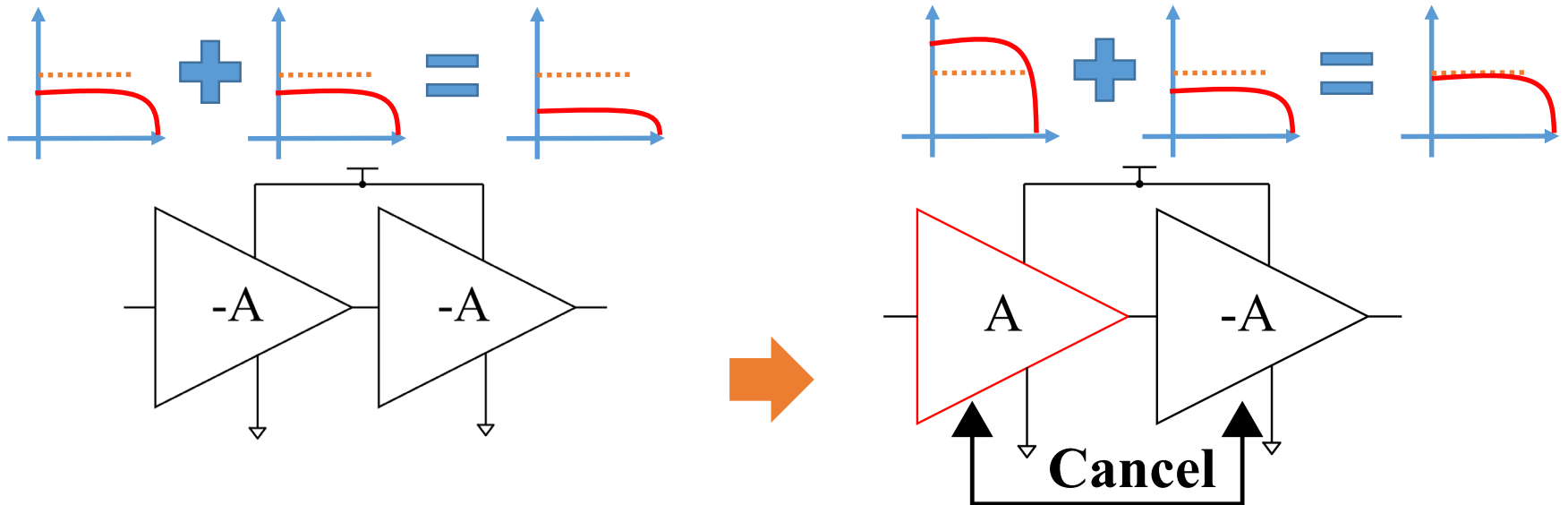
High performance extra circuits increase the costs.

- Power consumption
- Area
- Another power supply

► **We realize Supply-noise-tolerant TIA without extra circuits.**

# Our key idea

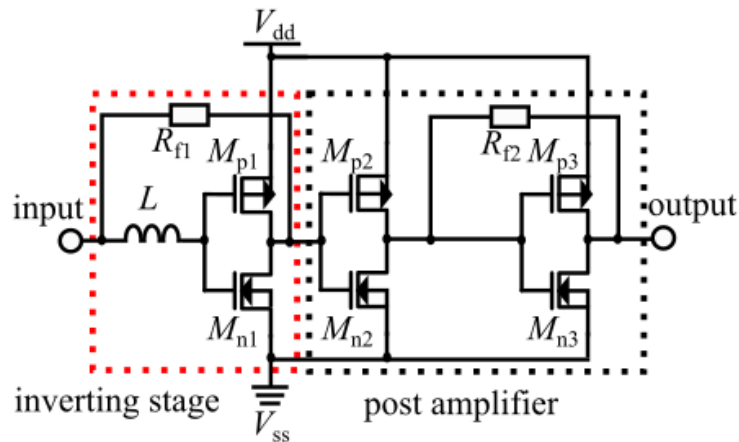
Invert the characteristic of circuit.



**How we invert the characteristic of TIA?**

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# The reference TIA



A combination of a inverting stage and post amplifier

The gain of the inverting stage

$$g_m R_f$$

Fig. Schematic of the reference TIA.

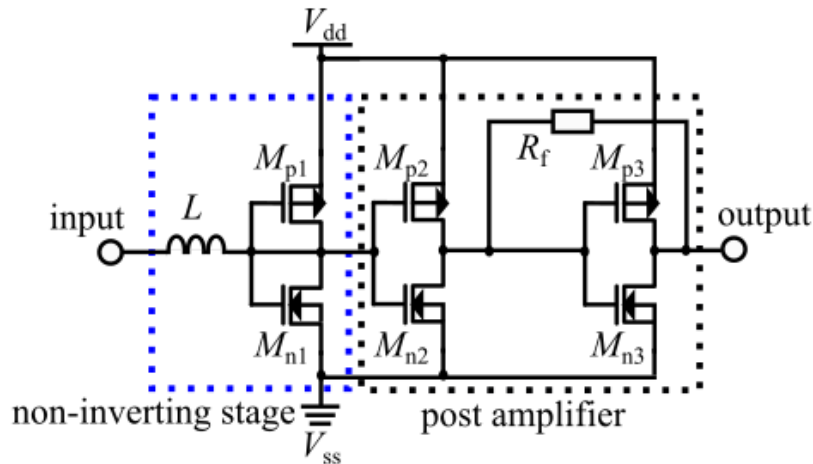
The supply voltage drops and the current through the MOS decreases.



The gain of the inverting stage and post amplifier decrease.

**The combination of a circuit that increases gain when the current decreases.**





A combination of a non-inverting stage and post amplifier

The gain of the non-inverting stage

▶  $\frac{1}{g_m}$

Fig. Schematic of the proposed TIA.

By supply voltage drop

- The gain of the non-inverting stage increases.
- The gain of post amplifier decreases.

↓  
**Cancel out the effects of power supply voltage drop**

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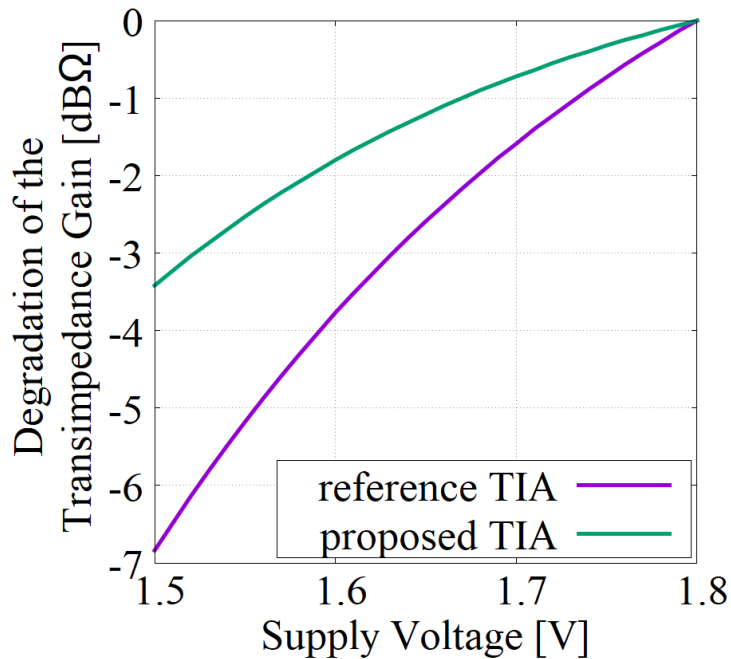


Fig. Characteristic of the supply voltage-Degradation of the gain.

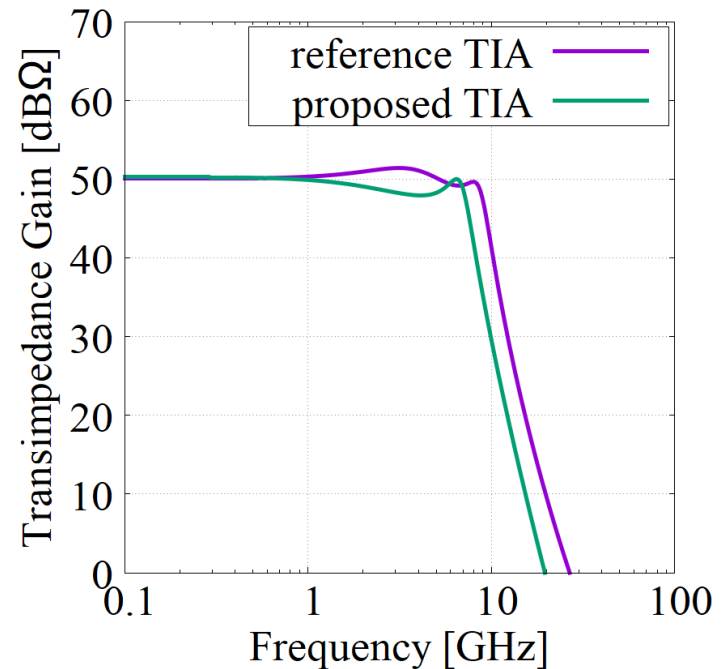
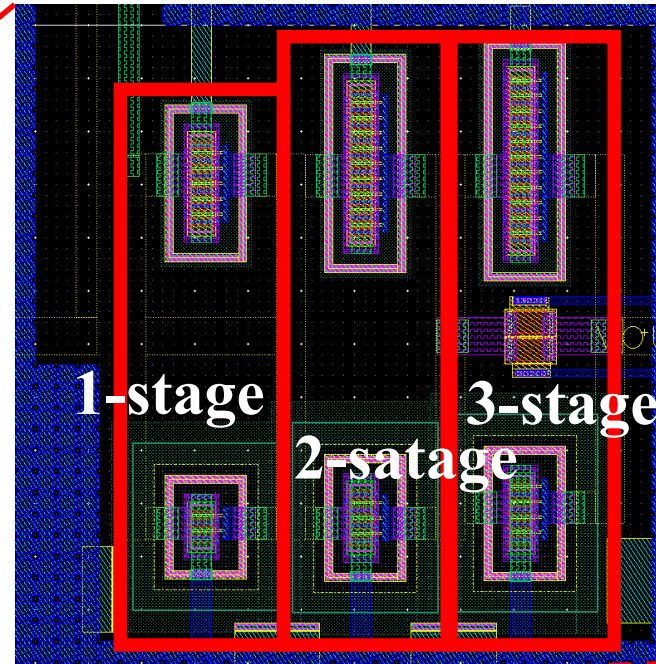
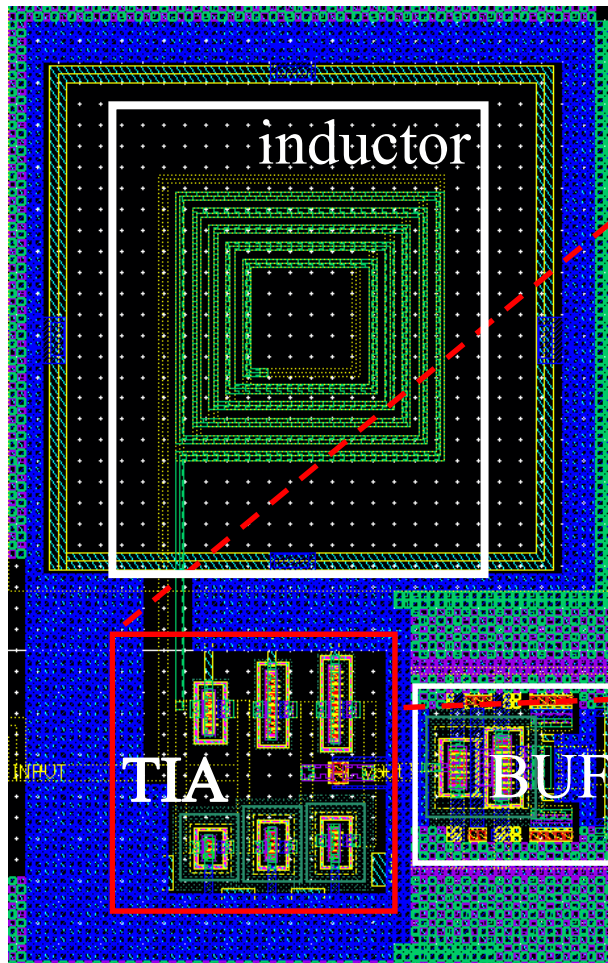


Fig. Frequency characteristics.

**Merit** : Tolerance to power supply variations

**Demerit** : Degradation of bandwidth

**Eye diagram of proposed TIA at 1.5V is good.**



The drain and gate terminals of the first stage are shorted.

Bandwidth extension using series peaking

Fig. Layout view of the proposed TIA and the output buffer.

## Design parameters (reference TIA)

$M_{n1}$	$M_{p1}$	$M_{n2}$	$M_{p2}$	$M_{n3}$	$M_{p3}$
10 $\mu\text{m}$	36 $\mu\text{m}$	10 $\mu\text{m}$	28 $\mu\text{m}$	12 $\mu\text{m}$	34 $\mu\text{m}$

resistance $R_{f1}, R_{f2}$	inductance $L$
350 $\Omega$	4 nH

## Performance (reference TIA)

Power consumption : 6 mW  
Gain : 50 dB $\Omega$   
Bandwidth : 9.0 GHz

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## Design parameters (proposed TIA)

$M_{n1}$	$M_{p1}$	$M_{n2}$	$M_{p2}$	$M_{n3}$	$M_{p3}$
6 $\mu\text{m}$	20 $\mu\text{m}$	12 $\mu\text{m}$	36 $\mu\text{m}$	14 $\mu\text{m}$	42 $\mu\text{m}$

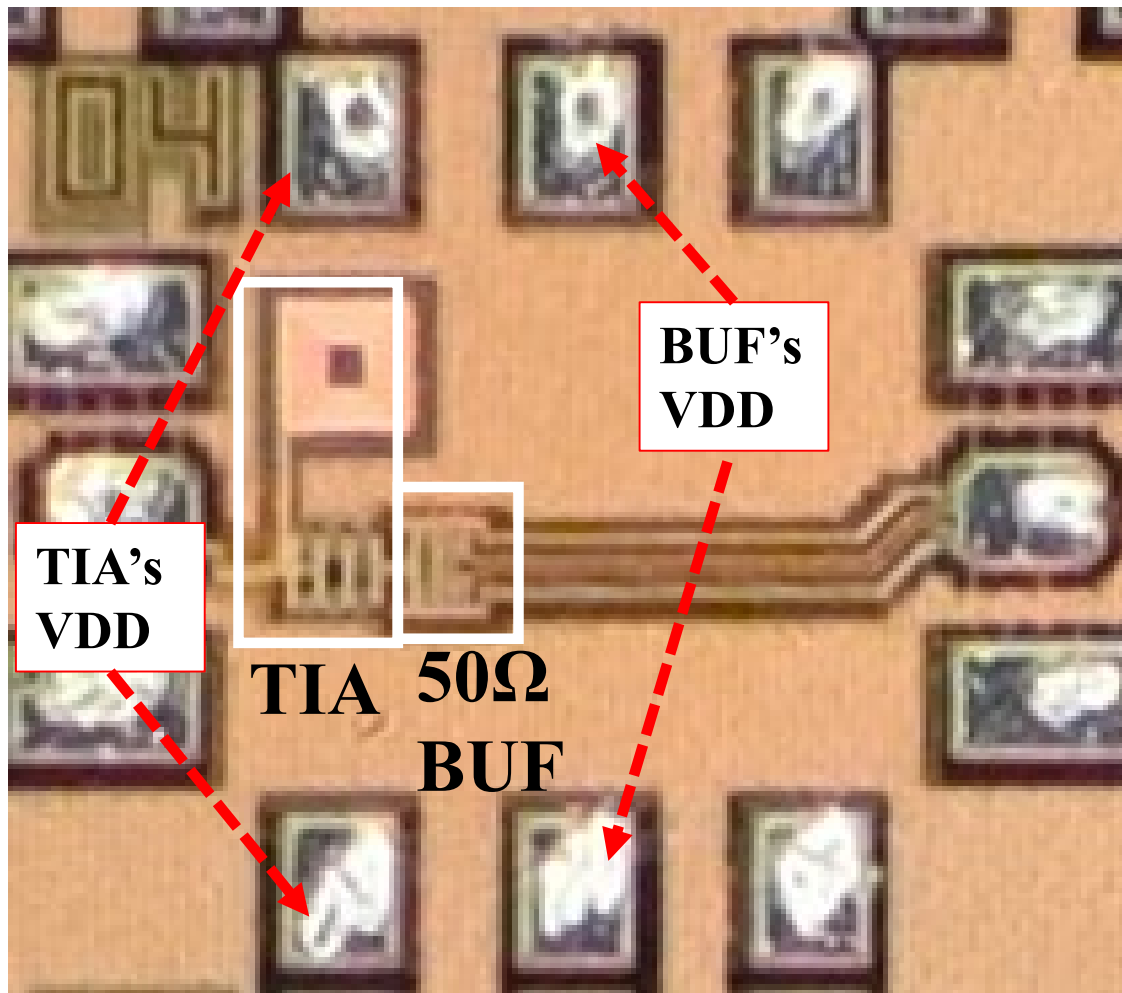
resistance $R_f$	inductance $L$
300 $\Omega$	7 nH

## Performance (proposed TIA)

Power consumption : 6 mW  
Gain : 50 dB $\Omega$   
Bandwidth : 7.3 GHz

**Constraints : 50 dB $\Omega$ , 6 mW**

**Designed for high power supply variation tolerance.**



- 180-nm CMOS
- On-wafer probing

Fig. Chip microphotograph of TIA and output buffer.

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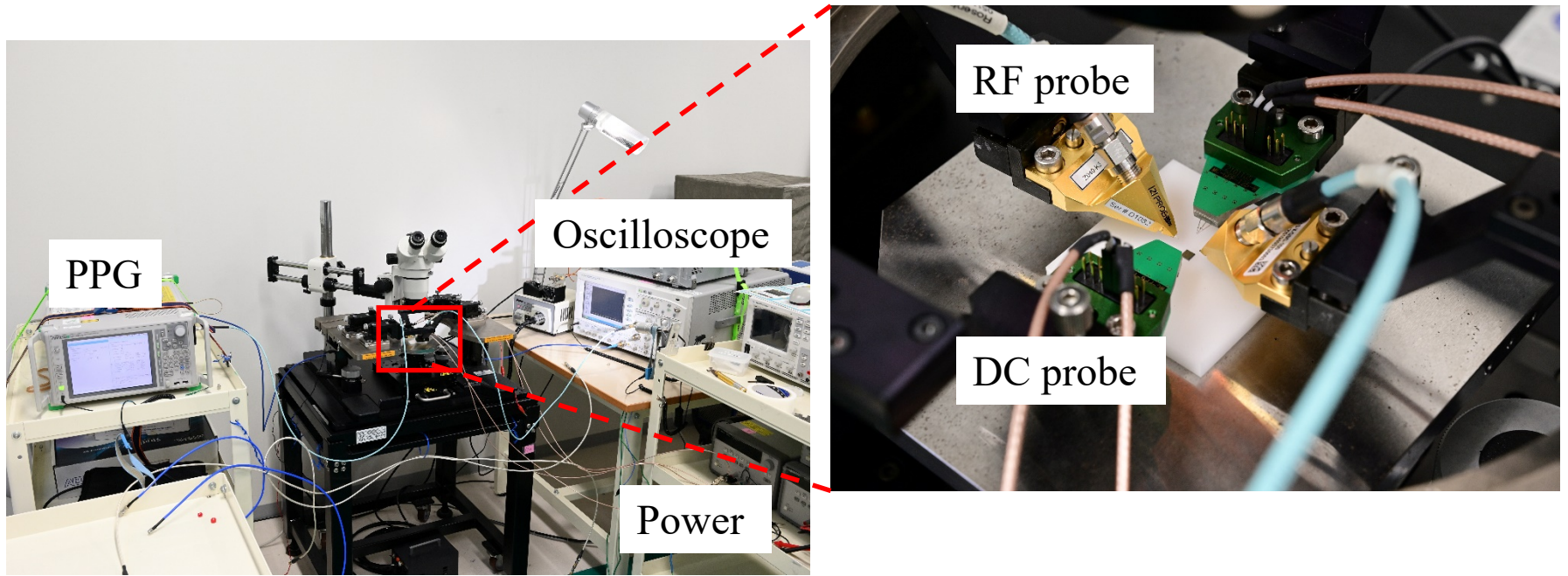
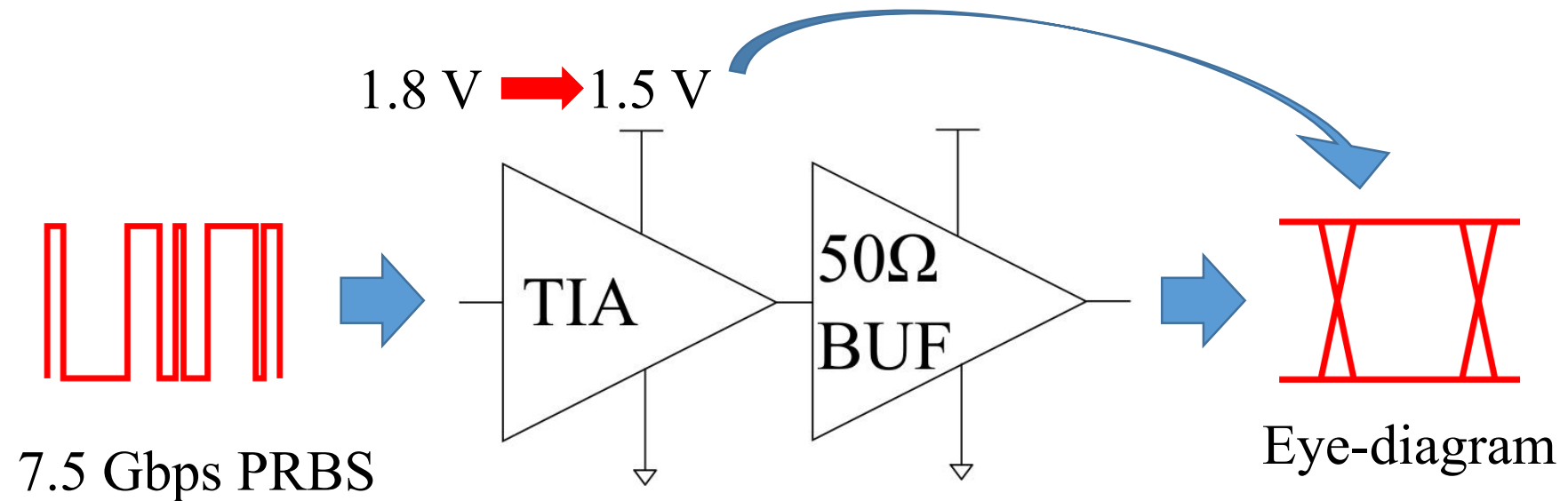


Fig. Photo of the measurement system.

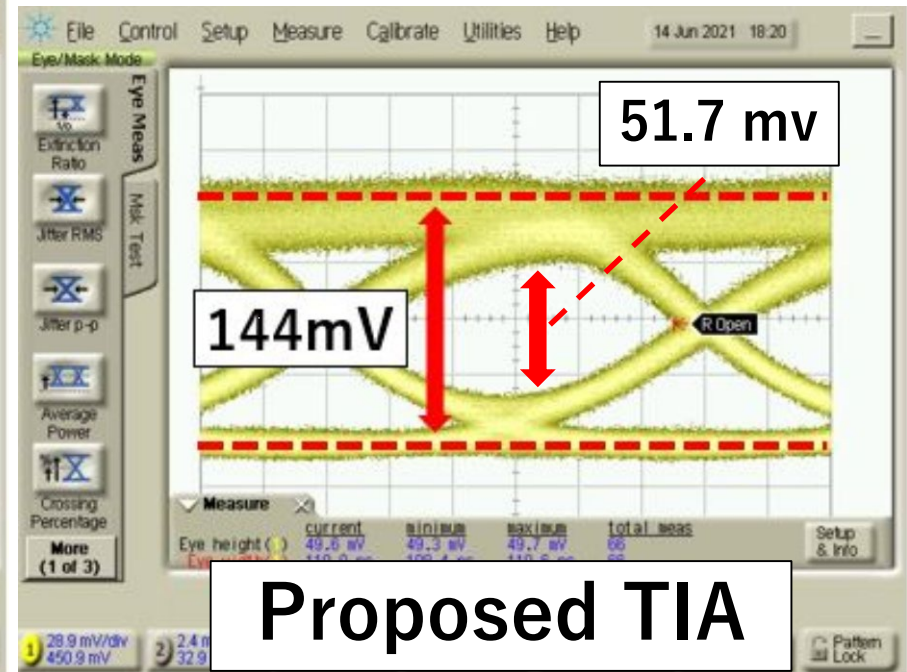
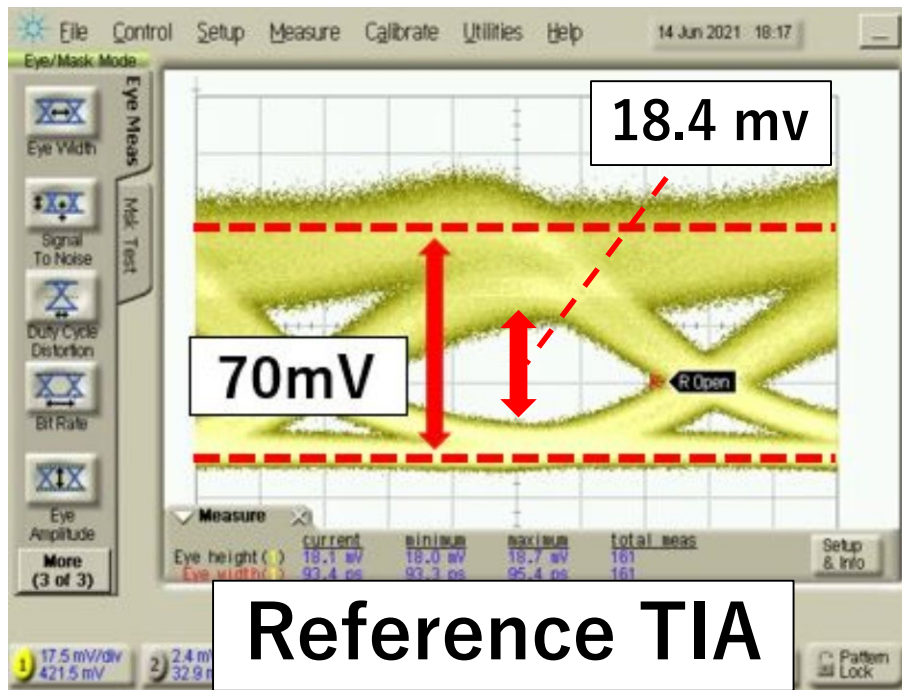
- Generate PRBS with Pulse Pattern Generator (PPG)
- Measure eye diagram with oscilloscope



- Standard voltage is 1.8 V.
- TIA's power supply considers voltage drop by noise.
- TIA and BUF power supplies are separated.



**Measure the effect of TIA supply voltage drop on the eye diagram.**



Amplitude (Low level-Hi level) : Improved 2 times  
Eye-opening voltage : Improved 3 times

**Proposed TIA is good eye diagram.**

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## **Our key idea :**

- Combining the non-inverting and the inverting amplifier circuits.
- Cancel the effect of power supply variation.

- 180-nm CMOS process
- On-wafer probing
- TIA's supply voltage drops to 1.5 V from 1.8 V.
- Input signal is 7.5 Gbps PRBS.

## **Measurement result :**

- Amplitude (Low level-Hi level) : Improved 2 times
- Eye-opening voltage : Improved 3 times

**Thank you for listening**